

Refine Search

10/674,478

Search Results -

Terms	Documents
L1 and fin	2

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L2

Refine Search

Recall Text

Clear

Interrupt

Search History

DATE: Monday, March 21, 2005 [Printable Copy](#) [Create Case](#)

<u>Set</u> <u>Name</u> side by side	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
	DB=USPT; PLUR=YES; OP=ADJ		
<u>L2</u>	L1 and fin	2	<u>L2</u>
<u>L1</u>	(silicide or silicided) near3 (source and drain and (dielectric or insulator or insulating))	293	<u>L1</u>

END OF SEARCH HISTORY

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 2 of 2 returned.

☐ 1. Document ID: US 6369418 B1

L2: Entry 1 of 2

File: USPT

Apr 9, 2002

US-PAT-NO: 6369418

DOCUMENT-IDENTIFIER: US 6369418 B1

TITLE: Formation of a novel DRAM cell

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 5998251 A

L2: Entry 2 of 2

File: USPT

Dec 7, 1999

US-PAT-NO: 5998251

DOCUMENT-IDENTIFIER: US 5998251 A

TITLE: Process and structure for embedded DRAM

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L1 and fin	2

Display Format: TI

Change Format

[Previous Page](#)

[Next Page](#)

[Go to Doc#](#)

Refine Search

Search Results -

Terms	Documents
L1 and source and drain	16

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L3

Refine Search

Recall Text 

Clear

Interrupt

Search History

DATE: Monday, March 21, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query
side by side

Hit Count Set Name
result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L3</u>	L1 and source and drain	16	<u>L3</u>
<u>L2</u>	L1 and source and drain	16	<u>L2</u>
<u>L1</u>	(silicide or silicided) near4 (buried near2 oxide)	17	<u>L1</u>

END OF SEARCH HISTORY

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 10 of 16 returned.

☐ 1. Document ID: US 6770495 B1

L3: Entry 1 of 16

File: USPT

Aug 3, 2004

US-PAT-NO: 6770495

DOCUMENT-IDENTIFIER: US 6770495 B1

TITLE: Method for revealing active regions in a SOI structure for DUT backside inspection

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	DOC	Draw D
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☐ 2. Document ID: US 6699758 B2

L3: Entry 2 of 16

File: USPT

Mar 2, 2004

US-PAT-NO: 6699758

DOCUMENT-IDENTIFIER: US 6699758 B2

TITLE: Semiconductor device and method for manufacturing the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	DOC	Draw D
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☐ 3. Document ID: US 6649976 B2

L3: Entry 3 of 16

File: USPT

Nov 18, 2003

US-PAT-NO: 6649976

DOCUMENT-IDENTIFIER: US 6649976 B2

TITLE: Semiconductor device having metal silicide film and manufacturing method thereof

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	DOC	Draw D
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☐ 4. Document ID: US 6518625 B1

L3: Entry 4 of 16

File: USPT

Feb 11, 2003

US-PAT-NO: 6518625

DOCUMENT-IDENTIFIER: US 6518625 B1

TITLE: Semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 5. Document ID: US 6486513 B1

L3: Entry 5 of 16

File: USPT

Nov 26, 2002

US-PAT-NO: 6486513

DOCUMENT-IDENTIFIER: US 6486513 B1

TITLE: Semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 6. Document ID: US 6472258 B1

L3: Entry 6 of 16

File: USPT

Oct 29, 2002

US-PAT-NO: 6472258

DOCUMENT-IDENTIFIER: US 6472258 B1

TITLE: Double gate trench transistor

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 7. Document ID: US 6433388 B1

L3: Entry 7 of 16

File: USPT

Aug 13, 2002

US-PAT-NO: 6433388

DOCUMENT-IDENTIFIER: US 6433388 B1

TITLE: Semiconductor device with self-aligned areas formed using a supplemental silicon overlayer

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 8. Document ID: US 6340829 B1

L3: Entry 8 of 16

File: USPT

Jan 22, 2002

US-PAT-NO: 6340829

DOCUMENT-IDENTIFIER: US 6340829 B1

TITLE: Semiconductor device and method for manufacturing the same

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 9. Document ID: US 6319805 B1

L3: Entry 9 of 16

File: USPT

Nov 20, 2001

US-PAT-NO: 6319805

DOCUMENT-IDENTIFIER: US 6319805 B1

TITLE: Semiconductor device having metal silicide film and manufacturing method thereof

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 10. Document ID: US 6051494 A

L3: Entry 10 of 16

File: USPT

Apr 18, 2000

US-PAT-NO: 6051494

DOCUMENT-IDENTIFIER: US 6051494 A

TITLE: Semiconductor device having metal silicide film

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Generate Collection

Print

Fwd Refs

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Generate OACS

Terms

Documents

L1 and source and drain

16

Display Format: TI

Change Format

[Previous Page](#)[Next Page](#)[Go to Doc#](#)

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 11 through 16 of 16 returned.

☐ 11. Document ID: US 5958505 A

L3: Entry 11 of 16

File: USPT

Sep 28, 1999

US-PAT-NO: 5958505

DOCUMENT-IDENTIFIER: US 5958505 A

TITLE: Layered structure with a silicide layer and process for producing such a layered structure

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	Draw	Draw
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☐ 12. Document ID: US 5659194 A

L3: Entry 12 of 16

File: USPT

Aug 19, 1997

US-PAT-NO: 5659194

DOCUMENT-IDENTIFIER: US 5659194 A

TITLE: Semiconductor device having metal silicide film

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	Draw	Draw
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☐ 13. Document ID: US 5238855 A

L3: Entry 13 of 16

File: USPT

Aug 24, 1993

US-PAT-NO: 5238855

DOCUMENT-IDENTIFIER: US 5238855 A

TITLE: Cross-point contact-free array with a high-density floating-gate structure

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	Draw	Draw
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☐ 14. Document ID: US 4992394 A

L3: Entry 14 of 16

File: USPT

Feb 12, 1991

US-PAT-NO: 4992394

DOCUMENT-IDENTIFIER: US 4992394 A

TITLE: Self aligned registration marks for integrated circuit fabrication

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw D
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☐ 15. Document ID: US 4696092 A

L3: Entry 15 of 16

File: USPT

Sep 29, 1987

US-PAT-NO: 4696092

DOCUMENT-IDENTIFIER: US 4696092 A

TITLE: Method of making field-plate isolated CMOS devices

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw D
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☐ 16. Document ID: US 4561170 A

L3: Entry 16 of 16

File: USPT

Dec 31, 1985

US-PAT-NO: 4561170

DOCUMENT-IDENTIFIER: US 4561170 A

TITLE: Method of making field-plate isolated CMOS devices

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw D
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Clear

Generate Collection

Print

Fwd Refs

Bkwd Refs

Generate OACS

Terms

Documents

L1 and source and drain

16

Display Format: TI

Change Format

[Previous Page](#)[Next Page](#)[Go to Doc#](#)